

F7756-VB Datasheet

Dual P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 30	0.036 at V _{GS} = - 10 V	- 5.2		
- 30	0.055 at V _{GS} = - 4.5 V	- 4.2		

FEATURES

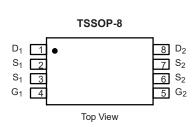
- · Halogen-free
- Trench Power MOSFETs

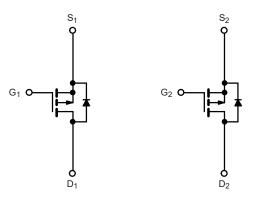


RoHS

APPLICATIONS

- · Load Switch
- Battery Switch





P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T	_A = 25 °C, unle	ss otherwise r	noted		
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	-	30	V
Gate-Source Voltage		V_{GS}	± 20		V
Continuous Dusin Compant /T = 450 °C/8	T _A = 25 °C	I _D	- 5.2	- 4.1	۸
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 4.2	- 3.6	
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.0	- 0.70	
Mariana Barra Birain Aire 8	T _A = 25 °C	D	1.14	0.83	W
Maximum Power Dissipation ^a	T _A = 70 °C	P _D	0.73	0.53	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55	to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana landian ta Ambianta	t ≤ 10 s	R _{thJA}	86	110	
Maximum Junction-to-Ambient ^a	Steady State		124	150	°C/W
Maximum Junction-to-Foot	Steady State	R_{thJF}	52	65	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



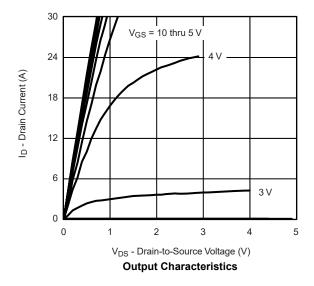
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static			I.	<u>'I</u>		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nΑ
Zana Cata Valtaria Dunin Comment		V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 5 V, V _{GS} = - 10 V	- 15			Α
	Б	V _{GS} = - 10 V, I _D = - 4.7 A		0.036		-
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 3.8 A		0.055		Ω
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 4.7 A		14		S
Diode Forward Voltage ^a	V_{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.74	- 1.1	V
Dynamic ^b	•			·!		
Total Gate Charge	Qg			13	20	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.7 \text{ A}$		3		nC
Gate-Drain Charge	Q_{gd}			5.8		
Gate Resistance	R_{g}	f = 1.0 MHz		4.6		Ω
Turn-On Delay Time	t _{d(on)}			13	20	
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	22	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_G = 6 Ω		52	80	ns
Fall Time	t _f			26	40	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.0 A, dl/dt = 100 A/μs		40	60	

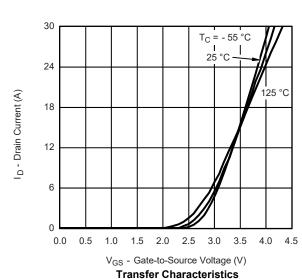
Notes:

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

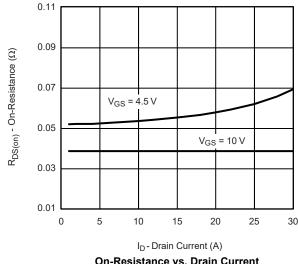
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



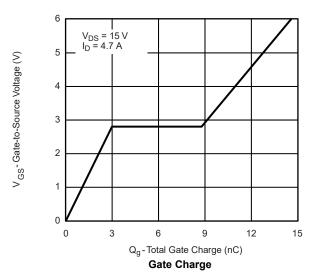


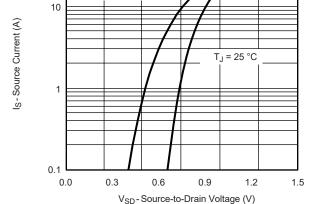


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



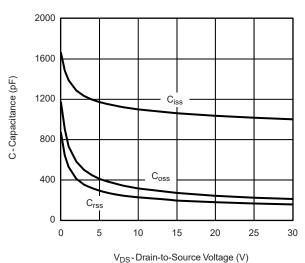
On-Resistance vs. Drain Current



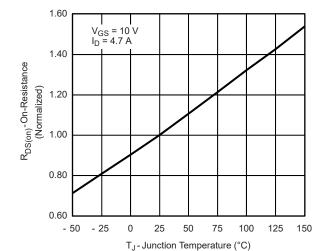


T_J = 150 °C

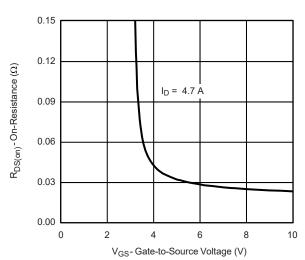
Source-Drain Diode Forward Voltage



Capacitance



On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

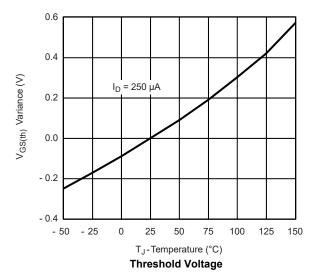
服务热线:400-655-8788

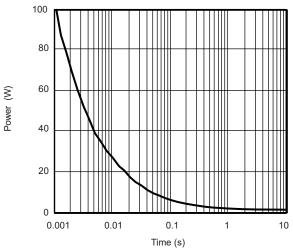
30

4

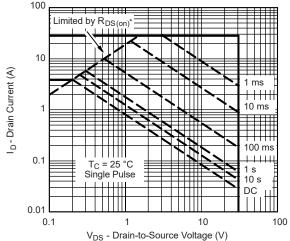


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

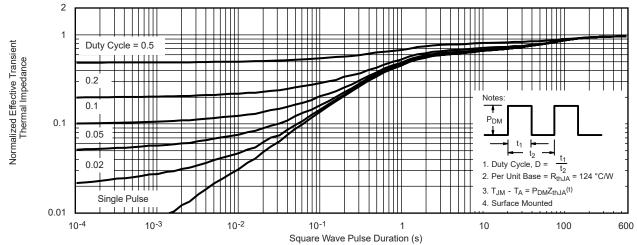




Single Pulse Power, Junction-to-Ambient



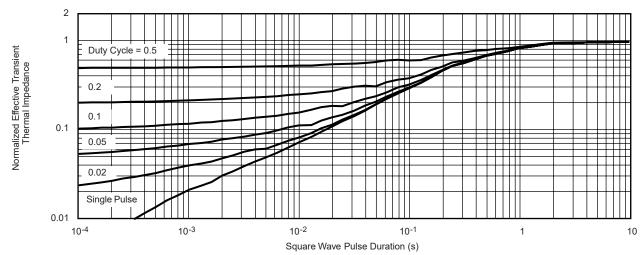
* V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified **Safe Operating Area, Junction-to-Case**



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

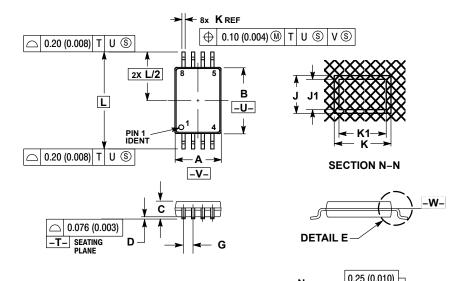


Normalized Thermal Transient Impedance, Junction-to-Foot



TSSOP-8





	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	4.30	4.50	0.169	0.177
С		1.10		0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.70	0.020	0.028
G	0.65 BSC		0.026 BSC	
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252	
M	0°	8°	0 8°	

N		IVI
"		
	~ F →	*
		1

DETAIL E



Disclaimer

All products due to improve reliability, function or design or for other reasons, product specifications and data are subject to change without notice.

Taiwan VBsemi Electronics Co., Ltd., branches, agents, employees, and all persons acting on its or their representatives (collectively, the "Taiwan VBsemi"), assumes no responsibility for any errors, inaccuracies or incomplete data contained in the table or any other any disclosure of any information related to the product.(www.VBsemi.com)

Taiwan VBsemi makes no guarantee, representation or warranty on the product for any particular purpose of any goods or continuous production. To the maximum extent permitted by applicable law on Taiwan VBsemi relinquished: (1) any application and all liability arising out of or use of any products; (2) any and all liability, including but not limited to special, consequential damages or incidental; (3) any and all implied warranties, including a particular purpose, non-infringement and merchantability guarantee.

Statement on certain types of applications are based on knowledge of the product is often used in a typical application of the general product VBsemi Taiwan demand that the Taiwan VBsemi of. Statement on whether the product is suitable for a particular application is non-binding. It is the customer's responsibility to verify specific product features in the products described in the specification is appropriate for use in a particular application. Parameter data sheets and technical specifications can be provided may vary depending on the application and performance over time. All operating parameters, including typical parameters must be made by customer's technical experts validated for each customer application. Product specifications do not expand or modify Taiwan VBsemi purchasing terms and conditions, including but not limited to warranty herein.

Unless expressly stated in writing, Taiwan VBsemi products are not intended for use in medical, life saving, or life sustaining applications or any other application. Wherein VBsemi product failure could lead to personal injury or death, use or sale of products used in Taiwan VBsemi such applications using client did not express their own risk. Contact your authorized Taiwan VBsemi people who are related to product design applications and other terms and conditions in writing.

The information provided in this document and the company's products without a license, express or implied, by estoppel or otherwise, to any intellectual property rights granted to the VBsemi act or document. Product names and trademarks referred to herein are trademarks of their respective representatives will be all.

Material Category Policy

Taiwan VBsemi Electronics Co., Ltd., hereby certify that all of the products are determined to be oHS compliant and meets the definition of restrictions under Directive of the European Parliament 2011/65 / EU, 2011 Nian. 6. 8 Ri Yue restrict the use of certain hazardous substances in electrical and electronic equipment (EEE) - modification, unless otherwise specified as inconsistent.(www.VBsemi.com)

Please note that some documents may still refer to Taiwan VBsemi RoHS Directive 2002/95 / EC. We confirm that all products identified as consistent with the Directive 2002/95 / EC European Directive 2011/65 /.

Taiwan VBsemi Electronics Co., Ltd. hereby certify that all of its products comply identified as halogen-free halogen-free standards required by the JEDEC JS709A. Please note that some Taiwanese VBsemi documents still refer to the definition of IEC 61249-2-21, and we are sure that all products conform to confirm compliance with IEC 61249-2-21 standard level JS709A.